

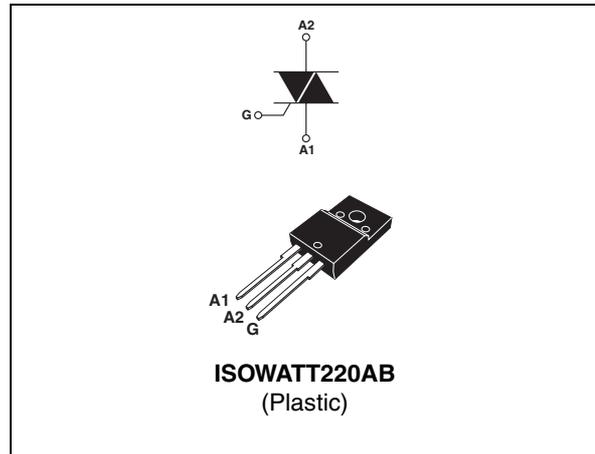
## 6 A Snubberless™ Triac

### Features

- $I_{T(RMS)} = 6\text{ A}$
- $V_{DRM} = V_{RRM} = 600\text{ and }800\text{ V}$

### Description

The high commutation performance of this device is based on Snubberless technology from ST. The T630W is especially suited for high inductance loads. This device complies with UL standards (Ref. E81734).



**Table 1. Device summary**

| Symbol            | Value       | Unit |
|-------------------|-------------|------|
| $I_{T(RMS)}$      | 6           | A    |
| $V_{DRM}/V_{RRM}$ | 600 and 800 | V    |
| $I_{GT}$          | 30          | mA   |

# 1 Characteristics

**Table 2. Absolute ratings (limiting values)**

| Symbol             | Parameter  |           | Value                     | Unit                           |                  |   |
|--------------------|--|-----------|---------------------------|--------------------------------|------------------|---|
| $I_{T(RMS)}$       | On-state rms current (full sine wave)  |           | $T_c = 105^\circ\text{C}$ | 6                              | A                |   |
| $I_{TSM}$          | Non repetitive surge peak on-state current (full cycle, $T_j$ initial = $25^\circ\text{C}$ ) | F = 50 Hz | t = 20 ms                 | 80                             | A                |   |
|                    |  | F = 60 Hz | t = 16.7 ms               | 84                             |                  |   |
| $I^2t$             | $I^2t$ Value for fusing  |           | $t_p = 10$ ms             | 36                             | A <sup>2</sup> s |   |
| di/dt              | Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ , $t_r \leq 100$ ns        |           | F = 120 Hz                | 50                             | A/ $\mu$ s       |   |
| $I_{GM}$           | Peak gate current  |           | $t_p = 20$ $\mu$ s        | $T_j = 125^\circ\text{C}$      | 4                | A |
| $P_{G(AV)}$        | Average gate power dissipation   |           | $T_j = 125^\circ\text{C}$ | 1                              | W                |   |
| $T_{stg}$<br>$T_j$ | Storage junction temperature range<br>Operating junction temperature range                   |           |                           | - 40 to + 150<br>- 40 to + 125 | $^\circ\text{C}$ |   |

**Table 3. Electrical characteristics ( $T_j = 25^\circ\text{C}$ , unless otherwise specified)**

| Symbol                              | Test conditions                        |                           | Quadrant     |      | Value | Unit       |
|-------------------------------------|--|---------------------------|--------------|------|-------|------------|
| $I_{GT}^{(1)}$                      | $V_D = 12$ V $R_L = 30$ $\Omega$       |                           | I - II - III | Max. | 30    | mA         |
| $V_{GT}$                            |  |                           | I - II - III | Max. | 1.3   | V          |
| $V_{GD}$                            | $V_D = V_{DRM}$ $R_L = 3.3$ k $\Omega$ | $T_j = 125^\circ\text{C}$ | I - II - III | Min. | 0.2   | V          |
| $I_H^{(2)}$                         | $I_T = 100$ mA                         |                           |              | Max. | 50    | mA         |
| $I_L$                               | $I_G = 1.2 I_{GT}$                     |                           | I - III      | Max. | 70    | mA         |
|                                     |  |                           | II           |      | 80    |            |
| dV/dt <sup>(2)</sup>                | $V_D = 67\% V_{DRM}$ gate open         | $T_j = 125^\circ\text{C}$ |              | Min. | 500   | V/ $\mu$ s |
| (di/dt) <sub>c</sub> <sup>(2)</sup> | Without snubber                        |                           |              | Min. | 4.5   | A/ms       |

1. Minimum  $I_{GT}$  is guaranteed at 5% of  $I_{GT}$  max.
2. For both polarities of A2 referenced to A1

**Table 4. Static characteristics**

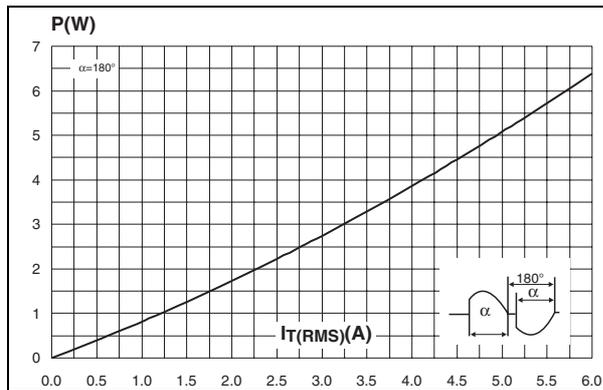
| Symbol                 | Test conditions     |                     |                           | Value | Unit |            |
|------------------------|---------------------|---------------------|---------------------------|-------|------|------------|
| $V_T^{(1)}$            | $I_{TM} = 8.5$ A    | $t_p = 380$ $\mu$ s | $T_j = 25^\circ\text{C}$  | Max.  | 1.4  | V          |
| $V_{t0}^{(1)}$         | Threshold voltage   |                     | $T_j = 125^\circ\text{C}$ | Max.  | 0.85 | V          |
| $R_d^{(1)}$            | Dynamic resistance  |                     | $T_j = 125^\circ\text{C}$ | Max.  | 50   | m $\Omega$ |
| $I_{DRM}$<br>$I_{RRM}$ | $V_{DRM} = V_{RRM}$ |                     | $T_j = 25^\circ\text{C}$  | Max.  | 5    | $\mu$ A    |
|                        |                     |                     | $T_j = 125^\circ\text{C}$ |       | 1    | mA         |

1. For both polarities of A2 referenced to A1

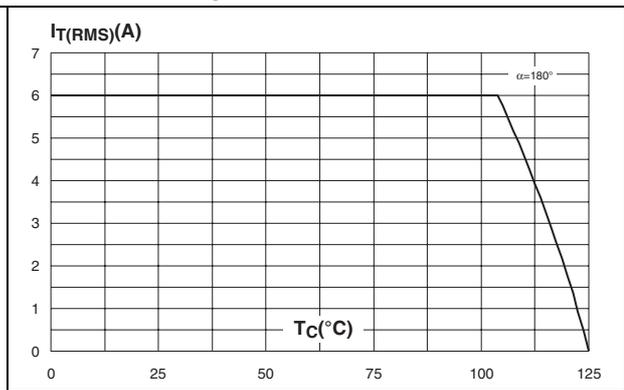
**Table 5. Thermal resistance**

| Symbol        | Parameter                                     | Value | Unit |
|---------------|---|-------|------|
| $R_{th(j-c)}$ | Junction to case (AC) (360° conduction angle) | 3.4   | °C/W |
| $R_{th(j-a)}$ | Junction to ambient                           | 50    | °C/W |

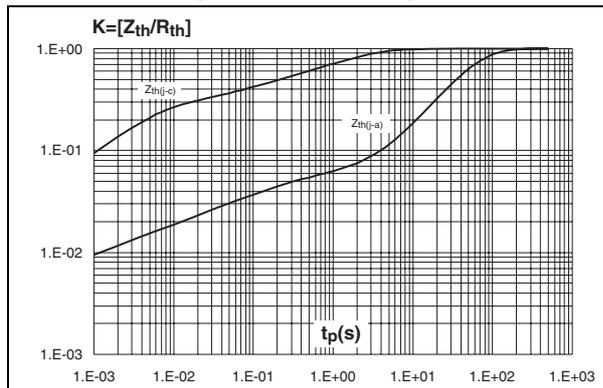
**Figure 1. Maximum power dissipation versus rms on-state current**



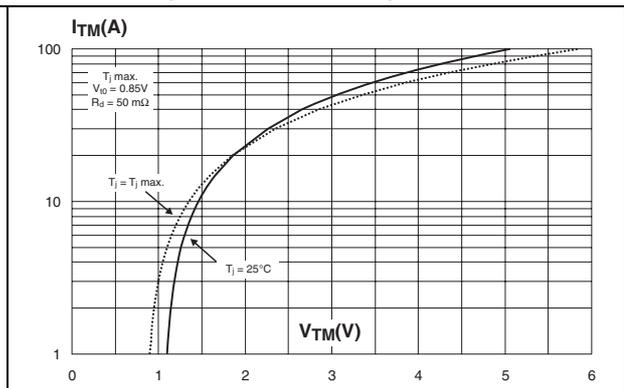
**Figure 2. On-state rms current versus case temperature**



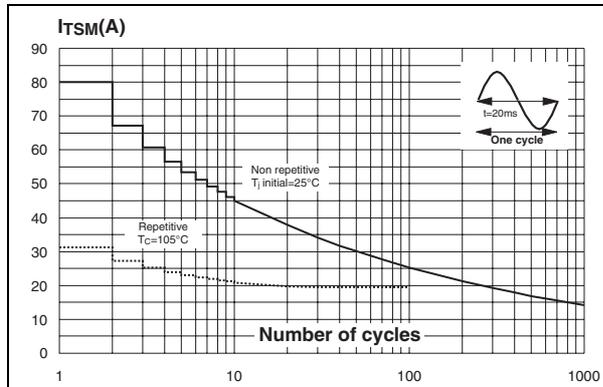
**Figure 3. Relative variation of thermal impedance versus pulse duration**



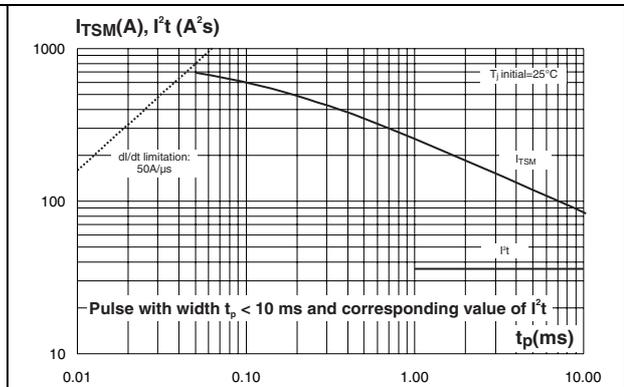
**Figure 4. On-state characteristics (maximum values)**



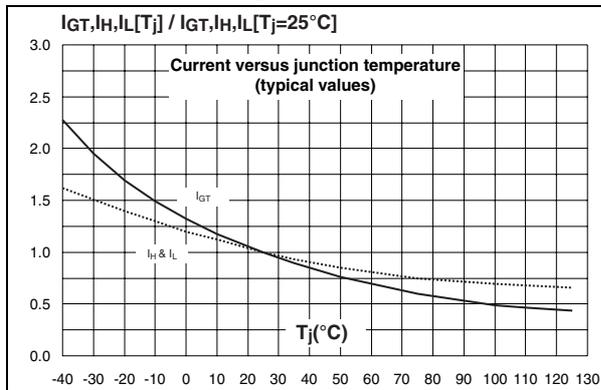
**Figure 5. Surge peak on-state current versus number of cycles**



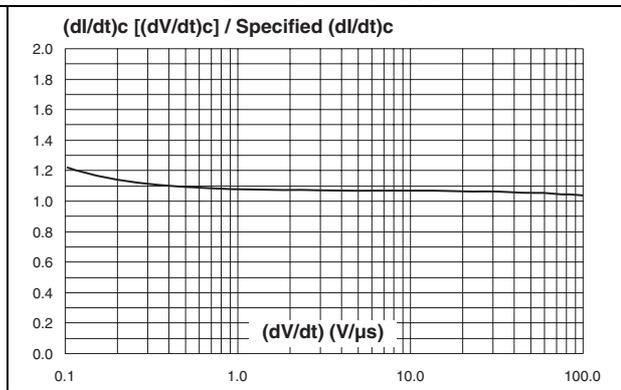
**Figure 6. Non-repetitive surge peak on-state current for a sinusoidal**



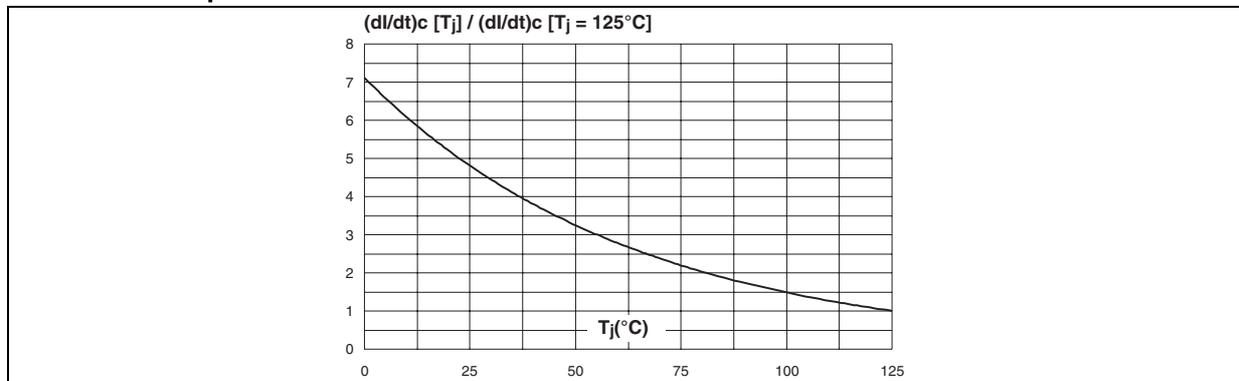
**Figure 7. Relative variation of gate trigger current, holding current and latching**



**Figure 8. Relative variation of critical rate of decrease of main current versus reapplied (dV/dt)<sub>c</sub> (typical value)**

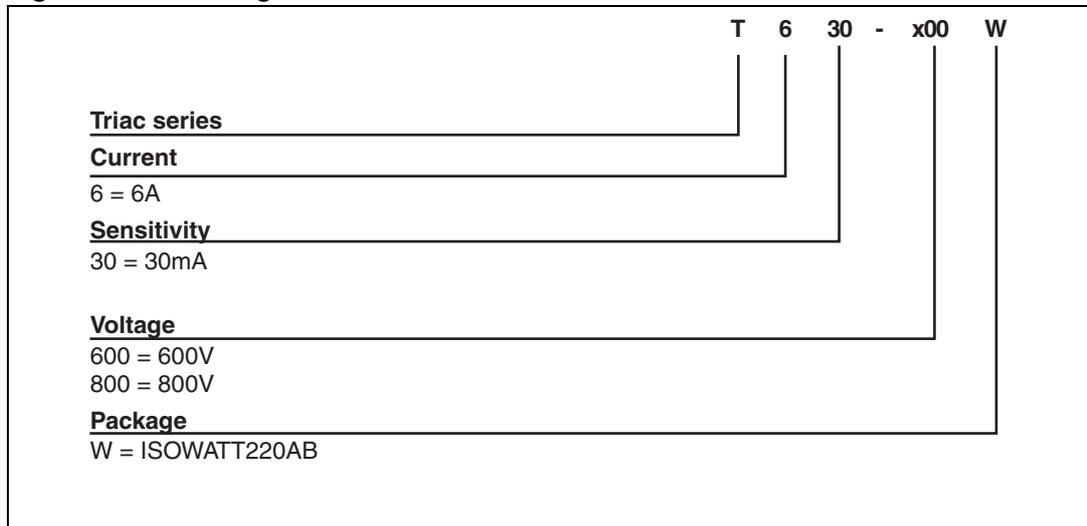


**Figure 9. Relative variation of critical rate of decrease of main current versus junction temperature**



## 2 Ordering information scheme

Figure 10. Ordering information scheme



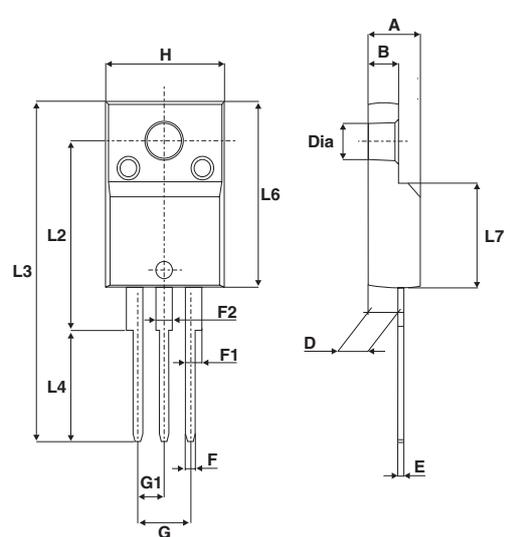
### 3 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque: 0.4 to 0.6 N·m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

**Table 6. ISOWATT220AB dimensions**

| Ref. | Dimensions  |       |            |       |
|------|-------------|-------|------------|-------|
|      | Millimeters |       | Inches     |       |
|      | Min.        | Max.  | Min.       | Max.  |
| A    | 4.40        | 4.60  | 0.173      | 0.181 |
| B    | 2.50        | 2.70  | 0.098      | 0.106 |
| D    | 2.50        | 2.75  | 0.098      | 0.108 |
| E    | 0.40        | 0.70  | 0.016      | 0.028 |
| F    | 0.75        | 1.00  | 0.030      | 0.039 |
| F1   | 1.15        | 1.70  | 0.045      | 0.067 |
| F2   | 1.15        | 1.70  | 0.045      | 0.067 |
| G    | 4.95        | 5.20  | 0.195      | 0.205 |
| G1   | 2.40        | 2.70  | 0.094      | 0.106 |
| H    | 10.00       | 10.40 | 0.394      | 0.409 |
| L2   | 16.00 typ.  |       | 0.630 typ. |       |
| L3   | 28.60       | 30.60 | 1.125      | 1.205 |
| L4   | 9.80        | 10.60 | 0.386      | 0.417 |
| L6   | 15.90       | 16.40 | 0.626      | 0.646 |
| L7   | 9.00        | 9.30  | 0.354      | 0.366 |
| Diam | 3.00        | 3.20  | 0.118      | 0.126 |



## 4 Ordering information

Table 7. Ordering information

| Order code | Marking  | Package      | Weight | Base qty | Delivery mode |
|------------|----------|--------------|--------|----------|---------------|
| T630-600W  | T630600W | ISOWATT220AB | 2.3 g  | 50       | Tube          |
| T630-800W  | T630800W |              |        |          |               |

## 5 Revision history

Table 8. Document revision history

| Date        | Revision | Changes  |
|-------------|----------|--|
| March-2004  | 2        | Last release.  |
| 09-Feb-2010 | 3        | Document split into T620W and T630W. This document provides information for the T630W. |

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